



SPN4812 N-Channel Enhancement Mode MOSFET

DESCRIPTION

The SPN4812 is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application , notebook computer power management and other battery powered circuits where high-side switching .

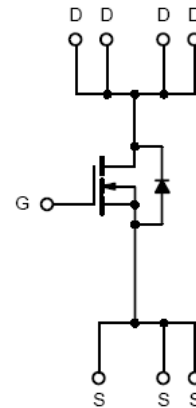
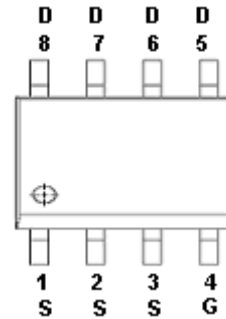
FEATURES

- ◆ 100V/12A, $R_{DS(ON)}=12m\Omega@V_{GS}=10V$
- ◆ 100V/12A, $R_{DS(ON)}=15m\Omega@V_{GS}=4.5V$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOP – 8P package design

APPLICATIONS

- DC/DC Converter
- Load Switch
- Synchronous Buck Converter
- SMPS Secondary Side Synchronous Rectifier
- Power Tool
- Motor Control

PIN CONFIGURATION(SOP – 8P)



PART MARKING





SPN4812

N-Channel Enhancement Mode MOSFET

PIN DESCRIPTION

Pin	Symbol	Description
1	S	Source
2	S	Source
3	S	Source
4	G	Gate
5	D	Drain
6	D	Drain
7	D	Drain
8	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPN4812S8RGB	SOP-8P	SPN4812

※ SPN4812S8RGB : 13" Tape Reel ; Pb – Free ; Halogen – Free

ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	100	V
Gate –Source Voltage	V _{GSS}	±20	V
Continuous Drain Current(T _J =150°C)	I _D	TA=25°C	12
		TA=70°C	8
Pulsed Drain Current	I _{DM}	60	A
Avalanche Energy, Single Pulse (L=0.1mH , Tc=25°C)	E _{AS}	22	mJ
Power Dissipation	P _D	TA=25°C	3.1
		TA=70°C	2.2
Operating Junction Temperature	T _J	-55/150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient (t ≤ 10s)	R _{θJA}	40	°C/W
Thermal Resistance-Junction to Ambient (steady state)		75	



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ELECTRICAL CHARACTERISTICS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	100			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.4	1.9	2.4	V
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$ $T_J=25^\circ C$			1	uA
		$V_{DS}=100V, V_{GS}=0V$ $T_J=100^\circ C$			100	
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=12A$		9.5	12	mΩ
		$V_{GS}=4.5V, I_D=10A$		11.5	15	
Forward Transconductance	g_{fs}	$V_{DS}=5V, I_D=12A$		45		S
Diode Forward Voltage	V_{SD}	$I_S=12A, V_{GS}=0V$		0.9	1.2	V
Dynamic						
Total Gate Charge	$Q_{g(10V)}$	$V_{DS}=50V, V_{GS}=10V$ $I_D=14A$		29		nC
Total Gate Charge	$Q_{g(4.5V)}$			14		
Gate-Source Charge	Q_{gs}			5		
Gate-Drain Charge	Q_{gd}			5		
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V$ $f=1MHz$		2275		pF
Output Capacitance	C_{oss}			162		
Reverse Transfer Capacitance	C_{rss}			7.9		
Turn-On Time	$t_{d(on)}$	$V_{DD}=50V,$ $I_D=14A, V_{GS}=10V$ $R_G=10\Omega$		8		nS
	t_r			3		
Turn-Off Time	$t_{d(off)}$			26		
	t_f			4		



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TYPICAL CHARACTERISTICS

Fig 1. Typical Output Characteristics

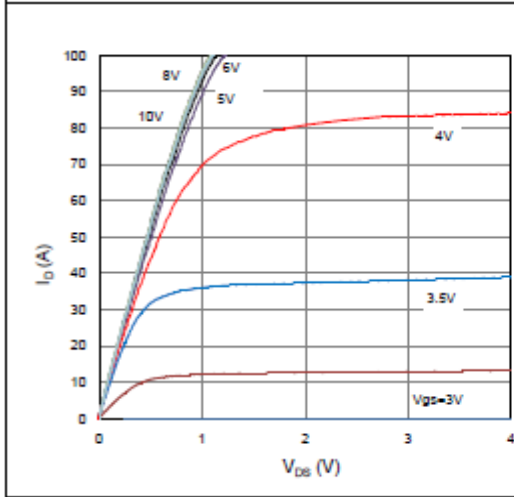


Figure 2. On-Resistance vs. Gate-Source Voltage

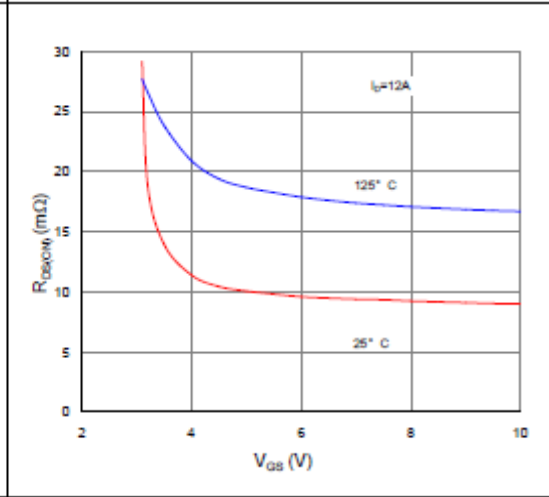


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

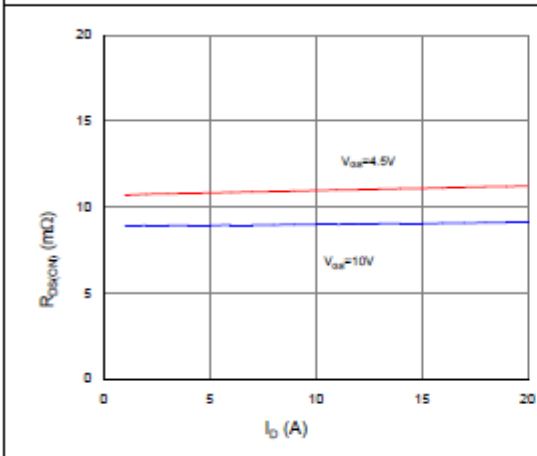


Figure 4. Normalized On-Resistance vs. Junction Temperature

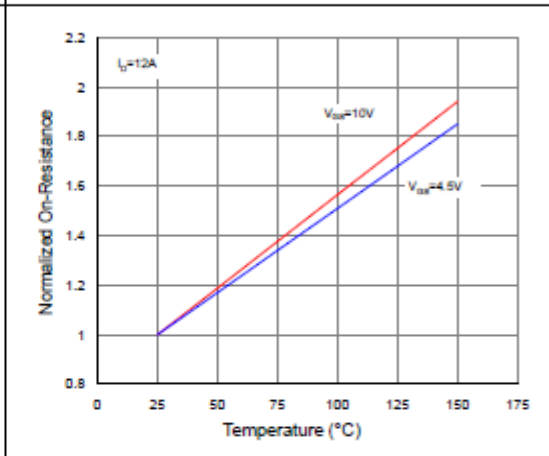


Figure 5. Typical Transfer Characteristics

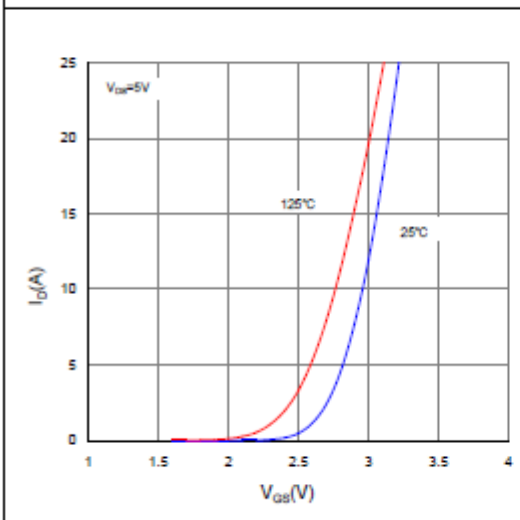
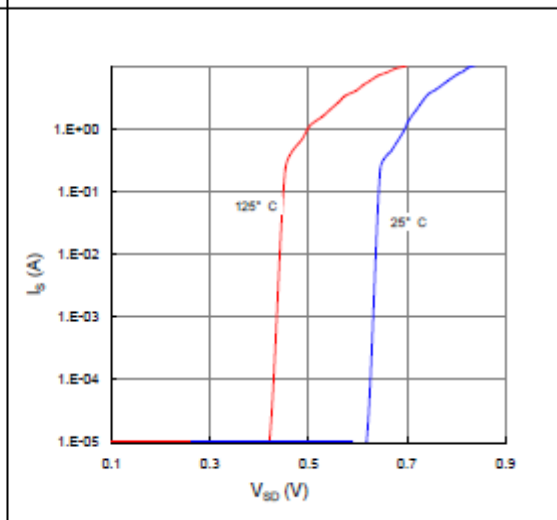


Figure 6. Typical Source-Drain Diode Forward Voltage





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TYPICAL CHARACTERISTICS

Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

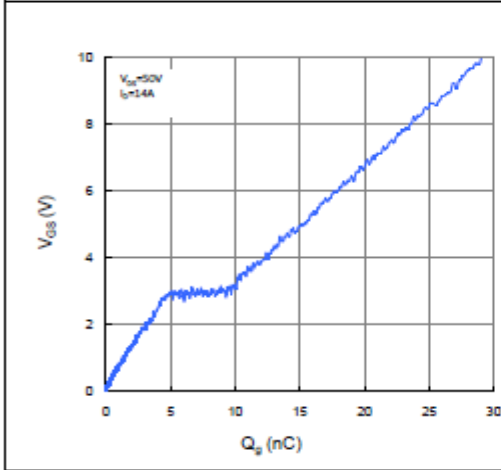


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

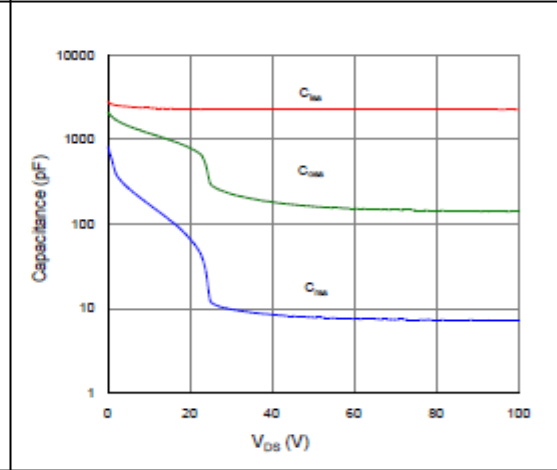


Figure 9. Maximum Safe Operating Area

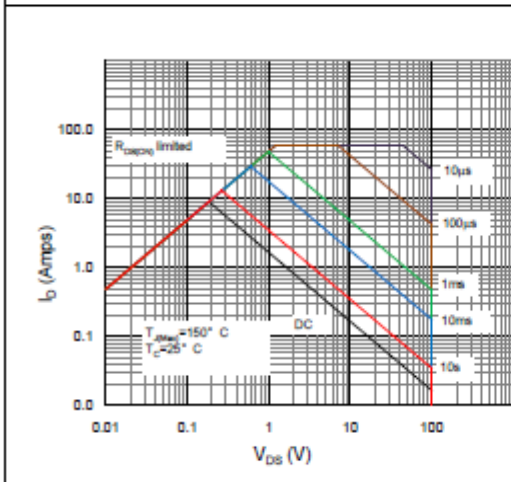


Figure 10. Maximum Drain Current vs. Case Temperature

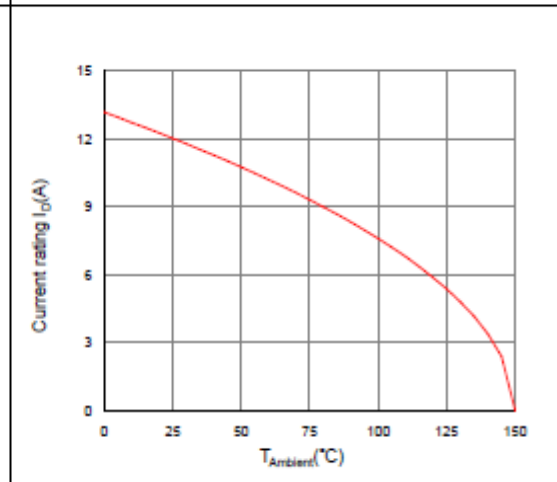
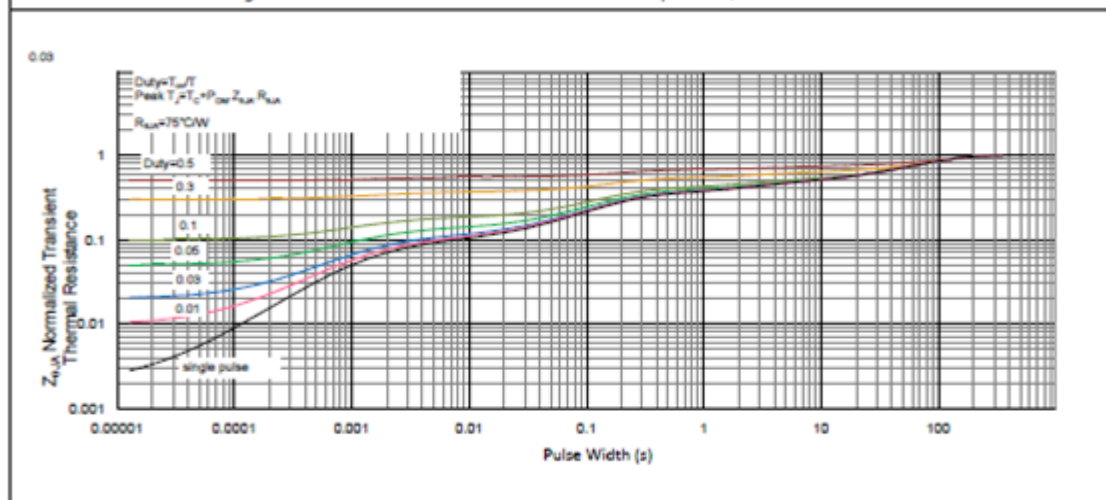


Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient

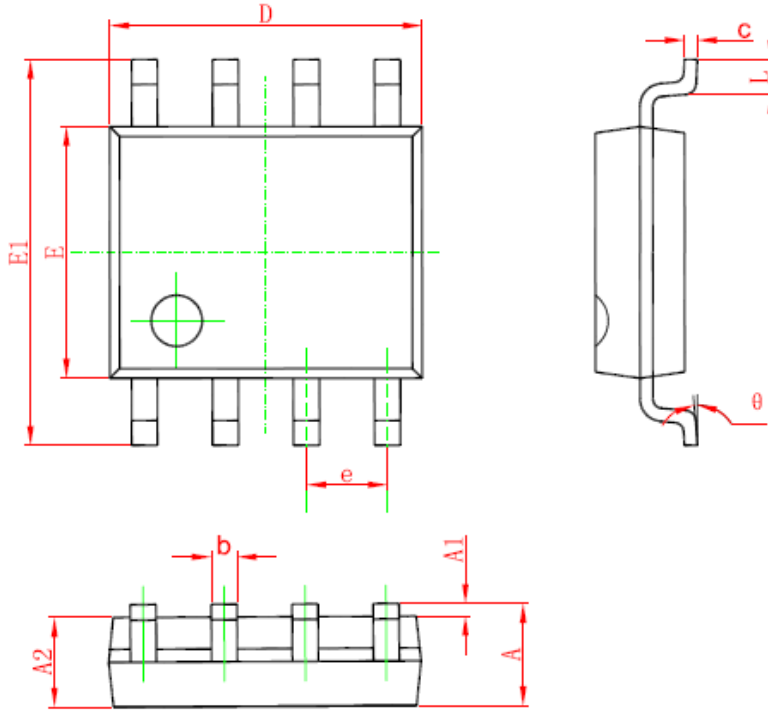




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SOP-8 PACKAGE OUTLINE



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



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